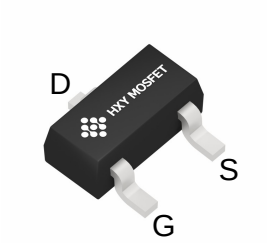
Description

The HXY3N10MI uses advaned trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



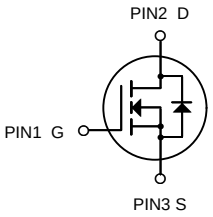
SOT-23-3L

General Features

V_{DS} = 100V I_D = 3A

$R_{DS(ON)}$ < 286mΩ @ V_{GS}=10V

$R_{DS(ON)}$ < 312mΩ @ V_{GS}=4.5V



N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY3N10MI	SOT-23-3L	03N10	3000

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	100	V
VGS	Gate-Source Voltage	±20	V
I_D	Drain Current-Continuous	3	A
IDM	Drain Current-Pulsed	1.4	A
P_D	Maximum Power Dissipation	2.3	W
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 175	°C
RθJA	Thermal Resistance,Junction-to-Ambient	100	°C/W

Electrical Characteristics (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1.0	1.5	2.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=2A	-	220	286	mΩ
		V_{GS}=4.5V, I_D=1A	-	223	312	
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=3A	-	5	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=25V,V_{GS}=0V, F=1.0MHz	-	320	-	PF
Output Capacitance	C_{oss}		-	20	-	PF
Reverse Transfer Capacitance	C_{rss}		-	14	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=30V, R_L=19Ω V_{GS}=10V,R_G=3Ω	-	13	-	nS
Turn-on Rise Time	t_r		-	53	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	17	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	V_{DS}=30V,I_D=3A, V_{GS}=10V	-	5.2	-	nC
Gate-Source Charge	Q_{gs}		-	1.2	-	nC
Gate-Drain Charge	Q_{gd}		-	1.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=3A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	3	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t ≤ 10 sec.

3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%

4 Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics (Curves)

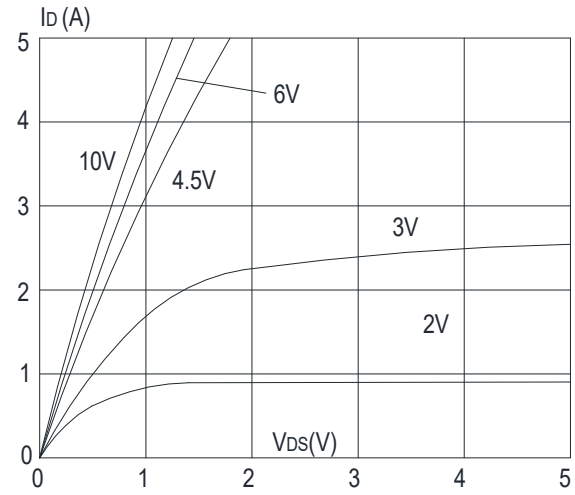


Figure1: Output Characteristics

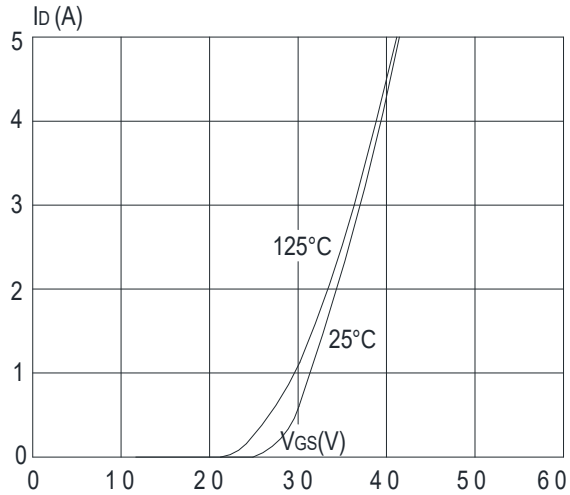


Figure 2: Typical Transfer Characteristics

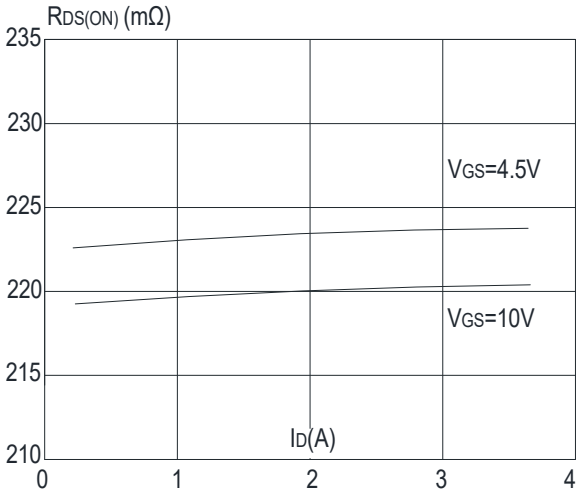


Figure 3: On-resistance vs. Drain Current

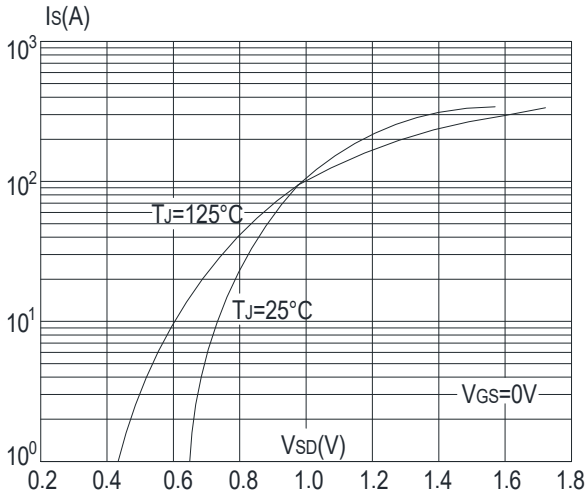


Figure 4: Body Diode Characteristics

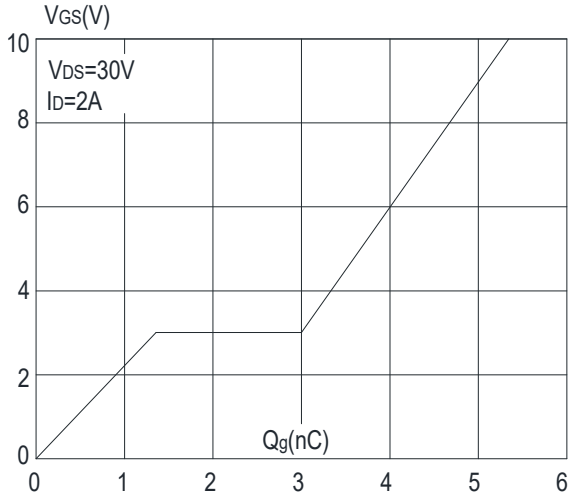


Figure 5: Gate Charge Characteristics

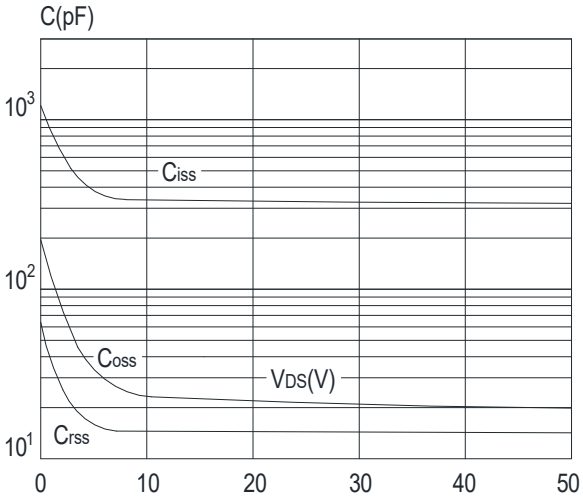


Figure 6: Capacitance Characteristics

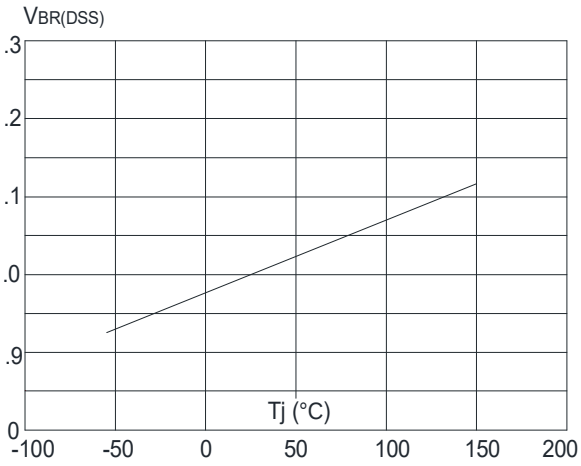


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

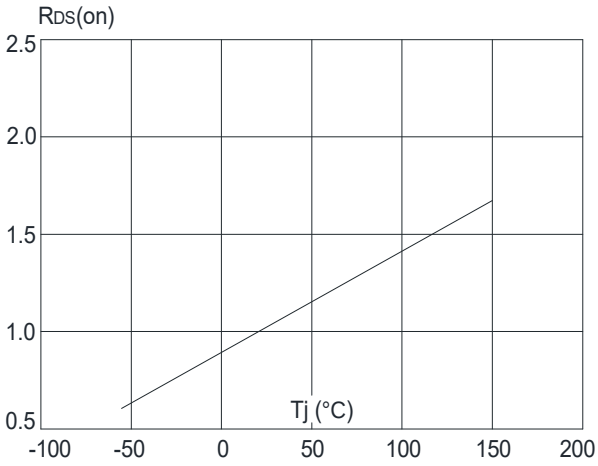


Figure 8: Normalized on Resistance vs. Junction Temperature

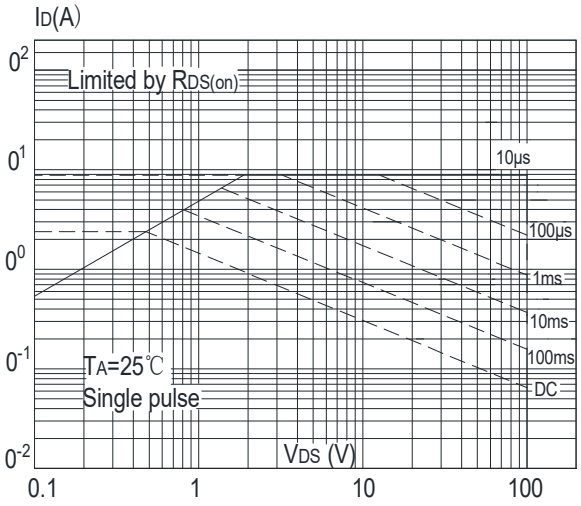


Figure 9: Maximum Safe Operating Area

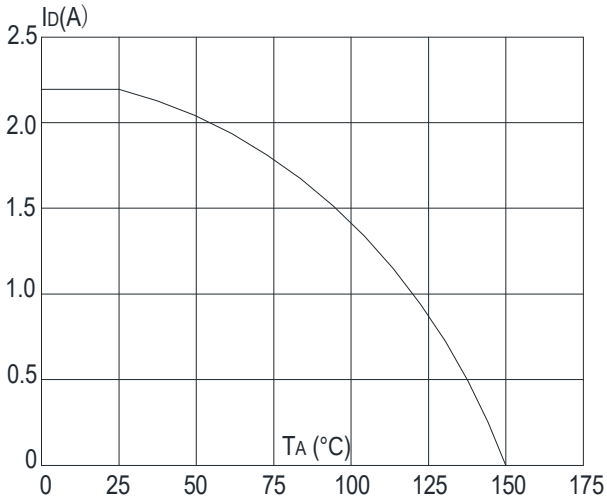


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

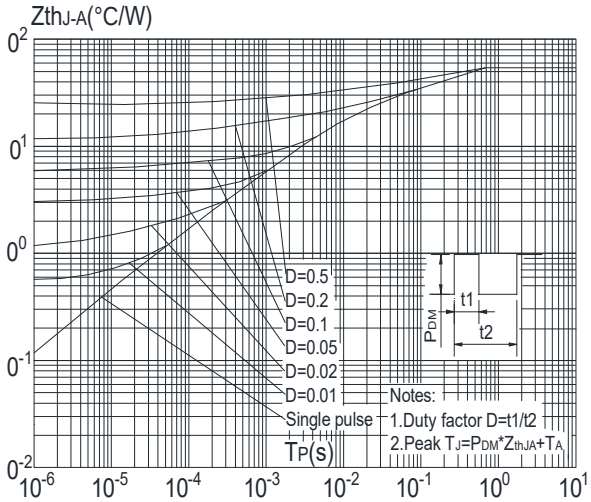
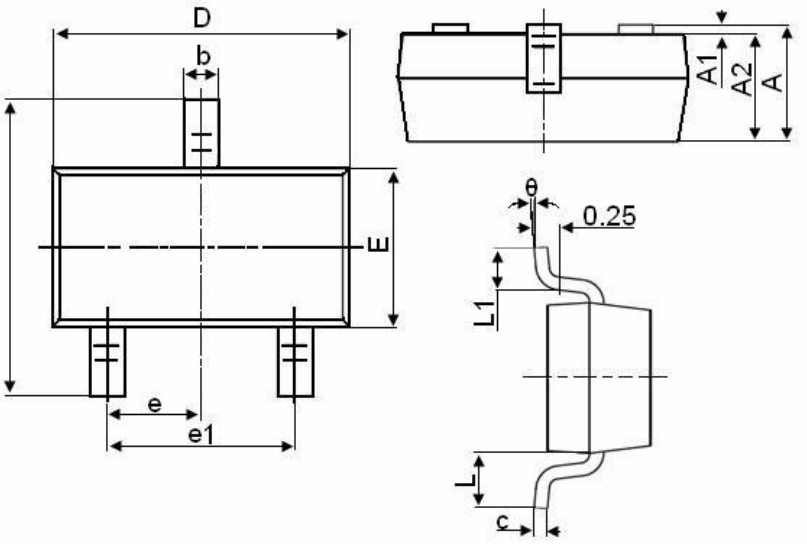


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

SOT-23-3L Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°

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